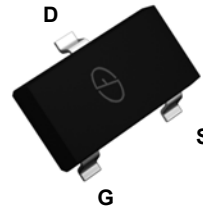
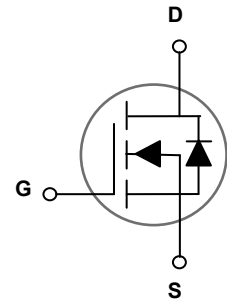


Main Product Characteristics

$V_{(BR)DSS}$	30V
$R_{DS(ON)}$	24m Ω
I_D	6.5A



SOT-23



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for MB/VGA/Core and load switch
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The SSF3912S utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current – Continuous (T _C =25°C)	I _D	6.5	A
Drain Current – Continuous (T _C =100°C)		4.1	A
Drain Current – Pulsed ¹	I _{DM}	26	A
Single Pulse Avalanche Energy ²	E _{AS}	32	mJ
Single Pulse Avalanche Current ²	I _{AS}	8	A
Power Dissipation (T _C =25°C)	P _D	1.56	W
Power Dissipation – Derate above 25°C	P _D	0.012	W/°C
Storage Temperature Range	T _{STG}	-55 to +150	°C
Operating Junction Temperature Range	T _J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	R _{θJA}	---	80	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=1\text{mA}$	---	0.04	---	$V/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
On Characteristics						
Static Drain-Source On-Resistance ³	$R_{DS(ON)}$	$V_{GS}=10V, I_D=6A$	---	20	24	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$	---	27	34	$m\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	-4	---	$mV/^\circ\text{C}$
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=4A$	---	6.5	---	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3, 4}	Q_g	$V_{DS}=15V, V_{GS}=4.5V, I_D=6A$	---	4.1	8	nC
Gate-Source Charge ^{3, 4}	Q_{gs}		---	1	2	
Gate-Drain Charge ^{3, 4}	Q_{gd}		---	2.1	4	
Turn-On Delay Time ^{3, 4}	$T_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, R_G=6\Omega, I_D=1A$	---	2.8	5	nS
Rise Time ^{3, 4}	T_r		---	7.2	14	
Turn-Off Delay Time ^{3, 4}	$T_{d(off)}$		---	15.8	30	
Fall Time ^{3, 4}	T_f		---	4.6	9	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	345	500	pF
Output Capacitance	C_{oss}		---	55	80	
Reverse Transfer Capacitance	C_{rss}		---	32	45	
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	3.2	6.4	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V, \text{Force Current}$	---	---	6.5	A
Pulsed Source Current ³	I_{SM}		---	---	26	A
Diode Forward Voltage ³	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_S=1A, di/dt=100A/\mu S, T_J=25^\circ\text{C}$	---	---	---	nS
Reverse Recovery Charge	Q_{rr}		---	---	---	nC

Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=1\text{mH}, I_{AS}=8A, R_G=25\Omega, \text{Starting } T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu S$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristics

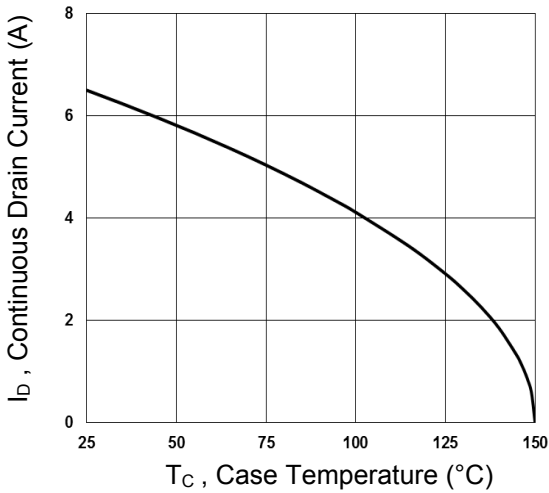


Fig.1 Continuous Drain Current vs. T_C

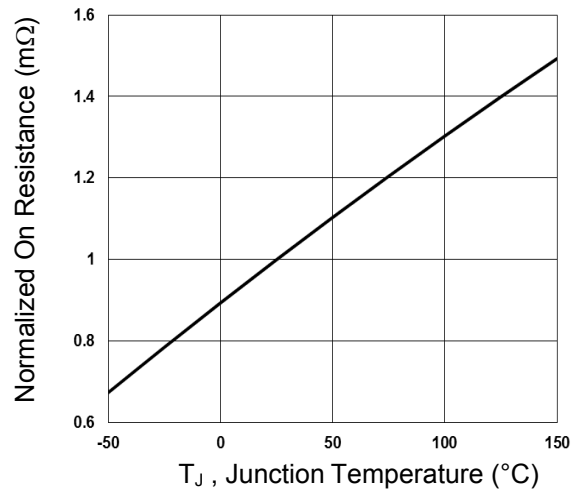


Fig.2 Normalized $R_{DS(ON)}$ vs. T_J

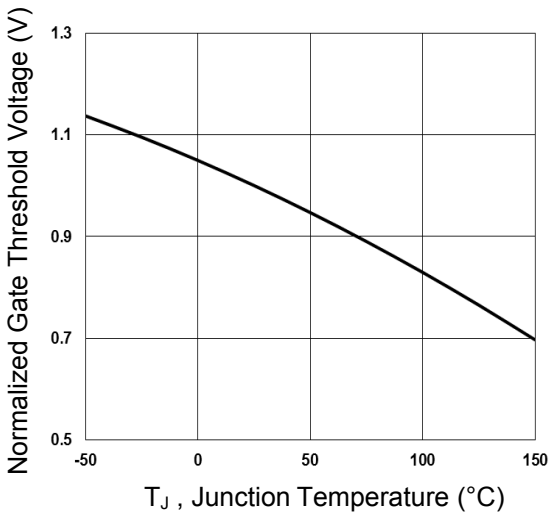


Fig.3 Normalized V_{th} vs. T_J

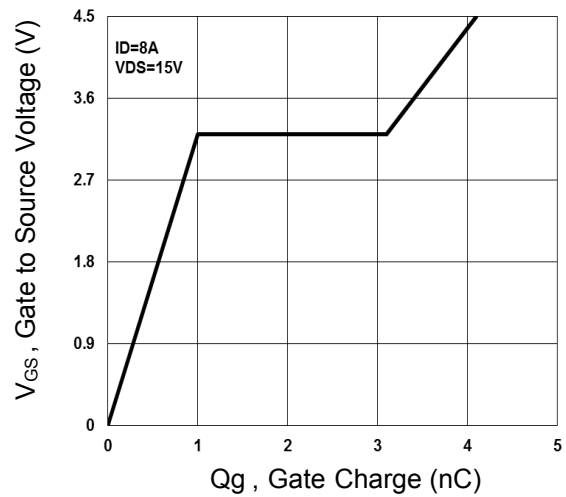


Fig.4 Gate Charge Waveform

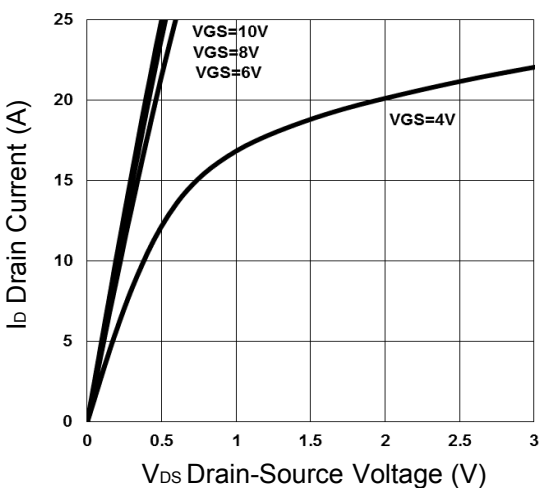


Fig.5 On Region Characteristics

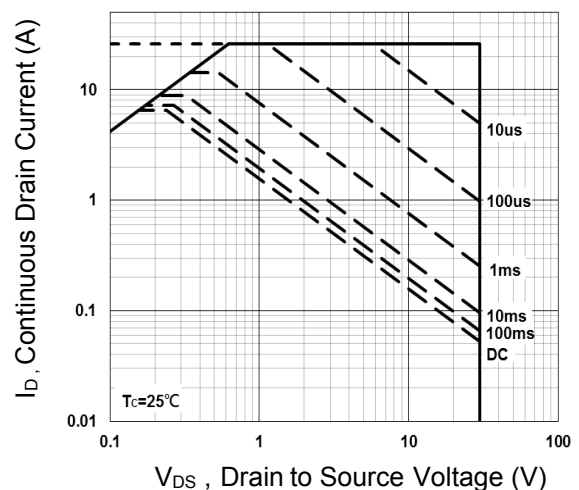


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristics

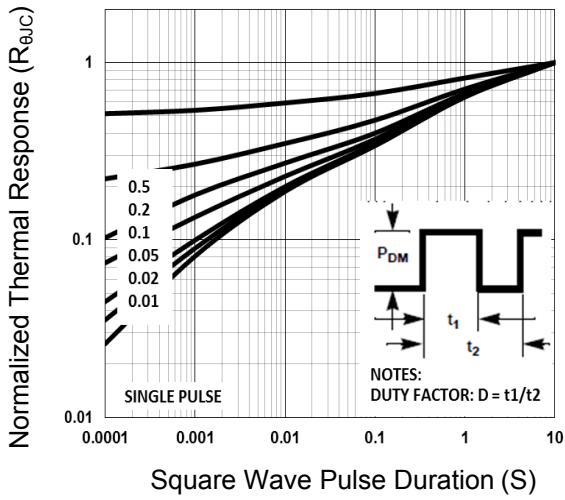


Fig.7 Normalized Transient Response

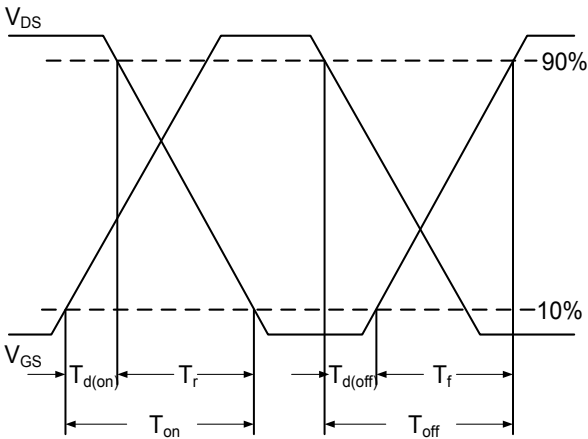


Fig.8 Switching Time Waveform

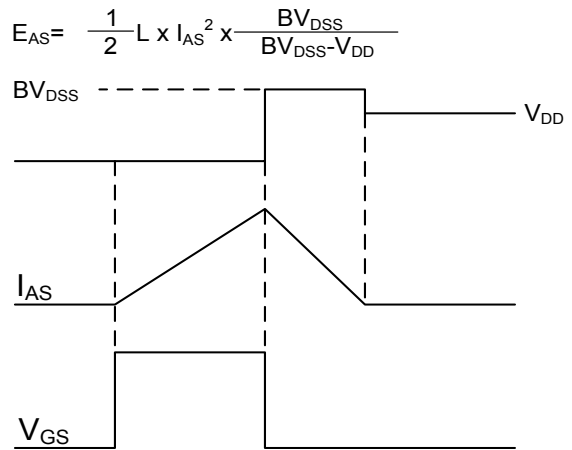
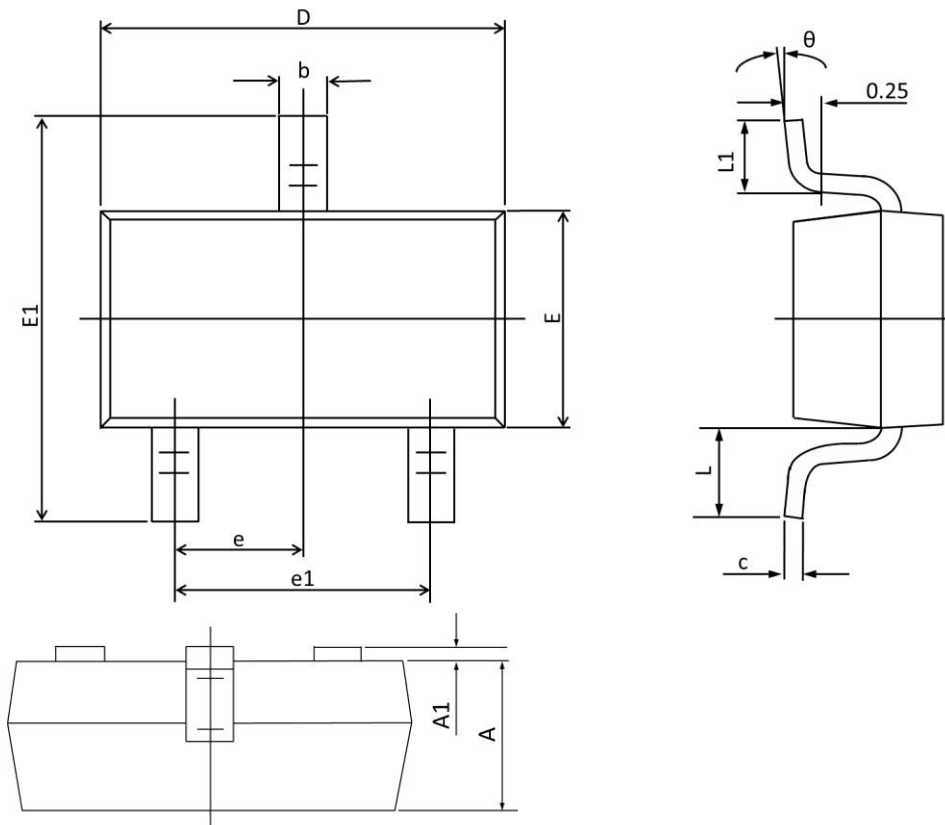


Fig.9 E_{AS} Waveform

Package Outline Dimensions

SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.000	0.035	0.039
A1	0.000	0.100	0.000	0.004
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°